



TK50E06K3A,S1X(S Information

Part Number TK50E06K3A,S1X(S

Manufacturer Toshiba Semiconductor and Storage

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 50A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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TK50E06K3A,S1X(S Specifications

Manufacturer Part NumberTK50E06K3A,S1X(SManufacturerToshiba Semiconductor and StorageCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesU-MOSIVFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C50ADrive Voltage (Max Rds On, Min Rds On)-Vgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs54nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs8.5 mOhm @ 25A, 10VOperating Temperature-Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series U-MOSIV FET Type N-Channel Technology MOSFET (Metal Oxide) four - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) - FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs N-Smohm @ 25A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case TO-220-3 Package / Case	Manufacturer Part Number	TK50E06K3A,S1X(S
Package TO-220-3 Series U-MOSIV FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 50A Drive Voltage (Max Rds On, Min Rds On) - Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) - FET Feature - Power Dissipation (Max) - Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature - Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Manufacturer	Toshiba Semiconductor and Storage
PackageTO-220-3SeriesU-MOSIVFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C50ADrive Voltage (Max Rds On, Min Rds On)-Vgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs54nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs8.5 mOhm @ 25A, 10VOperating Temperature-Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Category	Discrete Semiconductor Products
SeriesU-MOSIVFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C50ADrive Voltage (Max Rds On, Min Rds On)-Vgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs54nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs8.5 mOhm @ 25A, 10VOperating Temperature-Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 50A Drive Voltage (Max Rds On, Min Rds On) - Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) - FET Feature - Power Dissipation (Max) - Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package 70-220-3 Package / Case 700	Package	TO-220-3
Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 50A Drive Voltage (Max Rds On, Min Rds On) - Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) - FET Feature - Power Dissipation (Max) - Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature - Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case To-220-3	Series	U-MOSIV
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 50A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 50A Drive Voltage (Max Rds On, Min Rds On) - Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) - FET Feature - Power Dissipation (Max) - Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature - Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Set Smohm @ 25A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case TO-220-3	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 0perating Temperature - Mounting Type Through Hole Supplier Device Package Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	50A
Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) - FET Feature - Power Dissipation (Max) - Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature - Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	-
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) - FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature - Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Vgs(th) (Max) @ Id	-
Vgs (Max) - CFET Feature Factor	Gate Charge (Qg) (Max) @ Vgs	54nC @ 10V
FET Feature - Carrell Feature Feature Feature Feature Through Hole Feature Feature Feature Through Hole Feature Feat	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature - Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Vgs (Max)	-
Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature - Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	FET Feature	-
Operating Temperature Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Power Dissipation (Max)	-
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	8.5 mOhm @ 25A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3	Operating Temperature	-
Package / Case TO-220-3	Mounting Type	Through Hole
-	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

TK50E06K3A,S1X(S Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TK50E06K3A,S1X(S Payment Methods



















TK50E06K3A,S1X(S Shipping Methods













If you have any question about TK50E06K3A,S1X(S, please do not hesitate to contact us!

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